

ISL9V2040D3S / ISL9V2040S3S / ISL9V2040P3

EcoSPARK™ 200mJ, 400V, N-Channel Ignition IGBT

General Description

The ISL9V2040D3S, ISL9V2040S3S, and ISL9V2040P3 are the next generation ignition IGBTs that offer outstanding SCIS capability in the space saving D-Pak (TO-252), as well as the industry standard D²-Pak (TO-263) and TO-220 plastic packages. This device is intended for use in automotive ignition circuits, specifically as a coil driver. Internal diodes provide voltage clamping without the need for external components.

EcoSPARK™ devices can be custom made to specific clamp voltages. Contact your nearest Fairchild sales office for more information.

Formerly Developmental Type 49444

Applications

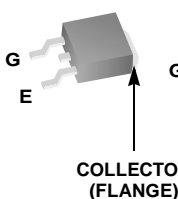
- Automotive Ignition Coil Driver Circuits
- Coil- On Plug Applications

Features

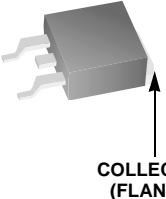
- Space saving D - Pak package available
- SCIS Energy = 200mJ at $T_J = 25^\circ\text{C}$
- Logic Level Gate Drive

Package

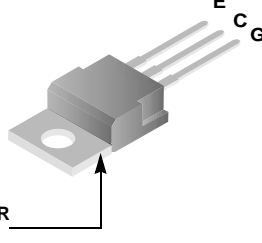
JEDEC TO-252AA
D-Pak



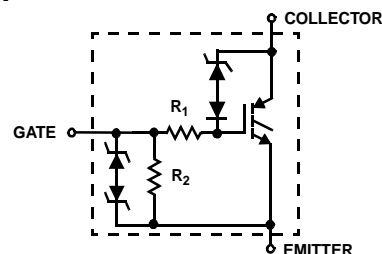
JEDEC TO-263AB
D²-Pak



JEDEC TO-220AB



Symbol



Device Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
BV_{CER}	Collector to Emitter Breakdown Voltage ($I_C = 1 \text{ mA}$)	430	V
BV_{ECS}	Emitter to Collector Voltage - Reverse Battery Condition ($I_C = 10 \text{ mA}$)	24	V
E_{SCIS25}	At Starting $T_J = 25^\circ\text{C}$, $I_{SCIS} = 11.5\text{A}$, $L = 3.0\text{mH}$	200	mJ
$E_{SCIS150}$	At Starting $T_J = 150^\circ\text{C}$, $I_{SCIS} = 8.9\text{A}$, $L = 3.0\text{mH}$	120	mJ
I_{C25}	Collector Current Continuous, At $T_C = 25^\circ\text{C}$, See Fig 9	10	A
I_{C110}	Collector Current Continuous, At $T_C = 110^\circ\text{C}$, See Fig 9	10	A
V_{GEM}	Gate to Emitter Voltage Continuous	± 10	V
P_D	Power Dissipation Total $T_C = 25^\circ\text{C}$	130	W
	Power Dissipation Derating $T_C > 25^\circ\text{C}$	0.87	W/ $^\circ\text{C}$
T_J	Operating Junction Temperature Range	-40 to 175	$^\circ\text{C}$
T_{STG}	Storage Junction Temperature Range	-40 to 175	$^\circ\text{C}$
T_L	Max Lead Temp for Soldering (Leads at 1.6mm from Case for 10s)	300	$^\circ\text{C}$
T_{pkg}	Max Lead Temp for Soldering (Package Body for 10s)	260	$^\circ\text{C}$
ESD	Electrostatic Discharge Voltage at 100pF, 1500Ω	4	kV

Package Marking and Ordering Information

Device Marking	Device	Package	Tape Width	Quantity
V2040D	ISL9V2040D3S	TO-252AA	16mm	2500
V2040S	ISL9V2040S3S	TO-263AB	24mm	800
V2040P	ISL9V2040P3	TO-220AB	-	-

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off State Characteristics

BV_{CER}	Collector to Emitter Breakdown Voltage	$I_C = 2\text{mA}$, $V_{GE} = 0$, $R_G = 1\text{K}\Omega$, See Fig. 15 $T_J = -40$ to 150°C	370	400	430	V	
BV_{CES}	Collector to Emitter Breakdown Voltage	$I_C = 10\text{mA}$, $V_{GE} = 0$, $R_G = 0$, See Fig. 15 $T_J = -40$ to 150°C	390	420	450	V	
BV_{ECS}	Emitter to Collector Breakdown Voltage	$I_C = -75\text{mA}$, $V_{GE} = 0\text{V}$, $T_C = 25^\circ\text{C}$	30	-	-	V	
BV_{GES}	Gate to Emitter Breakdown Voltage	$I_{GES} = \pm 2\text{mA}$	± 12	± 14	-	V	
I_{CER}	Collector to Emitter Leakage Current	$V_{CER} = 250\text{V}$, $R_G = 1\text{K}\Omega$ See Fig. 11	$T_C = 25^\circ\text{C}$	-	-	25	μA
		$T_C = 150^\circ\text{C}$	-	-	1	mA	
I_{ECS}	Emitter to Collector Leakage Current	$V_{EC} = 24\text{V}$, See Fig. 11	$T_C = 25^\circ\text{C}$	-	-	1	mA
			$T_C = 150^\circ\text{C}$	-	-	40	mA
R_1	Series Gate Resistance		-	70	-	Ω	
R_2	Gate to Emitter Resistance		10K	-	26K	Ω	

On State Characteristics

$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	$I_C = 6\text{A}$, $V_{GE} = 4\text{V}$	$T_C = 25^\circ\text{C}$, See Fig. 3	-	1.45	1.9	V
$V_{CE(SAT)}$	Collector to Emitter Saturation Voltage	$I_C = 10\text{A}$, $V_{GE} = 4.5\text{V}$	$T_C = 150^\circ\text{C}$ See Fig. 4	-	1.95	2.3	V

Dynamic Characteristics

Q _{G(ON)}	Gate Charge	I _C = 10A, V _{CE} = 12V, V _{GE} = 5V, See Fig. 14		-	12	-	nC
V _{GE(TH)}	Gate to Emitter Threshold Voltage	I _C = 1.0mA, V _{CE} = V _{GE} , See Fig. 10	T _C = 25°C	1.3	-	2.3	V
			T _C = 150°C	0.75	-	1.8	V
V _{GEP}	Gate to Emitter Plateau Voltage	I _C = 10A, V _{CE} = 12V		-	3.4	-	V

Switching Characteristics

$t_{d(ON)R}$	Current Turn-On Delay Time-Resistive	$V_{CE} = 14\text{V}$, $R_L = 1\Omega$ $V_{GE} = 5\text{V}$, $R_G = 1\text{K}\Omega$ $T_J = 25^\circ\text{C}$	-	0.61	-	μs
t_{riseR}	Current Rise Time-Resistive		-	2.17	-	μs
$t_{d(OFF)L}$	Current Turn-Off Delay Time-Inductive	$V_{CE} = 300\text{V}$, $L = 500\mu\text{H}$, $V_{GE} = 5\text{V}$, $R_G = 1\text{K}\Omega$ $T_J = 25^\circ\text{C}$, See Fig. 12	-	3.64	-	μs
t_{fL}	Current Fall Time-Inductive		-	2.36	-	μs
SCIS	Self Clamped Inductive Switching	$T_J = 25^\circ\text{C}$, $L = 3.0\text{mH}$, $R_G = 1\text{K}\Omega$, $V_{GE} = 5\text{V}$, See Fig. 1 & 2	-	-	200	mJ

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance Junction-Case	TO-252, TO-263, TO-220	-	-	1.15	$^\circ\text{C/W}$
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Typical Performance Curves (Continued)

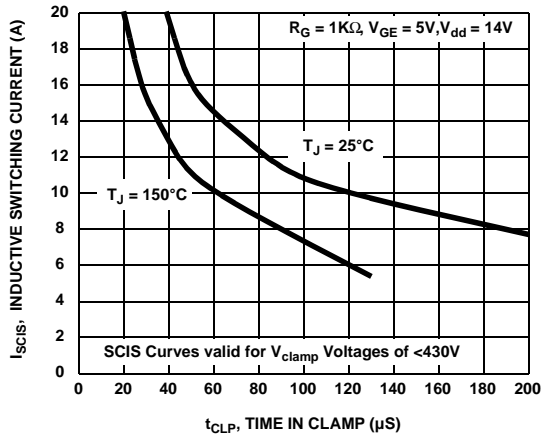


Figure 1. Self Clamped Inductive Switching Current vs Time in Clamp

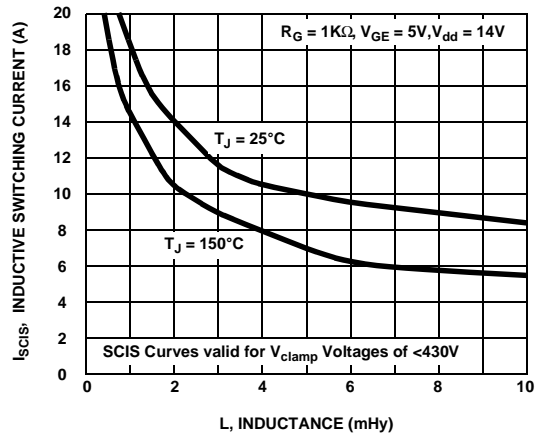


Figure 2. Self Clamped Inductive Switching Current vs Inductance

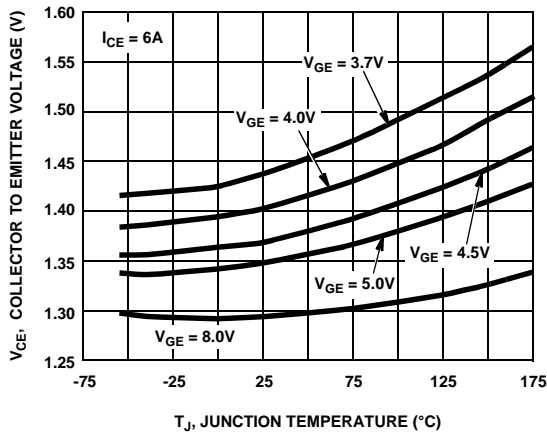


Figure 3. Collector to Emitter On-State Voltage vs Junction Temperature

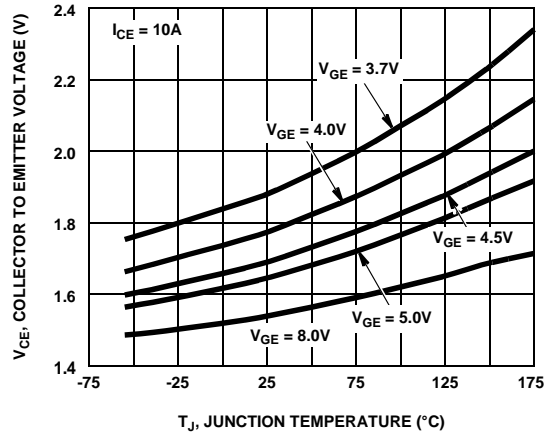


Figure 4. Collector to Emitter On-State Voltage vs Junction Temperature

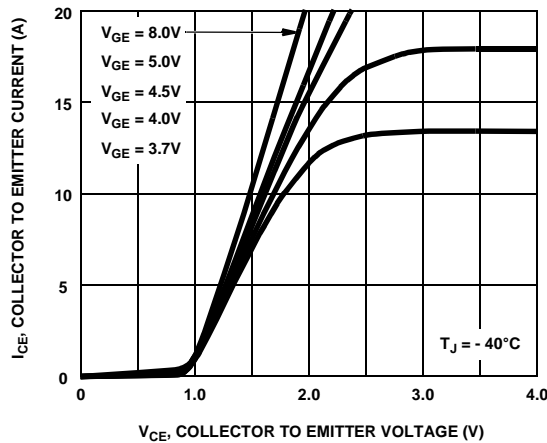


Figure 5. Collector to Emitter On-State Voltage vs Collector Current

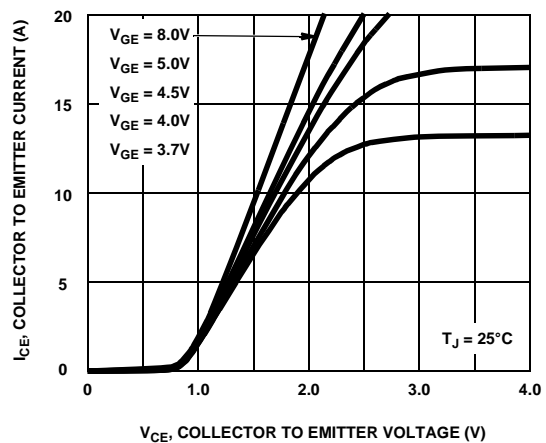


Figure 6. Collector to Emitter On-State Voltage vs Collector Current

Typical Performance Curves (Continued)

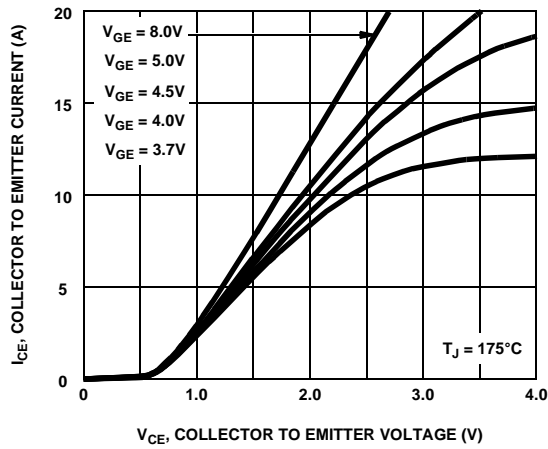


Figure 7. Collector to Emitter On-State Voltage vs Collector Current

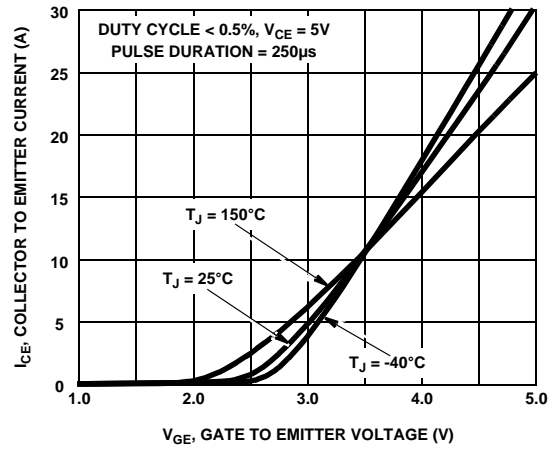


Figure 8. Transfer Characteristics

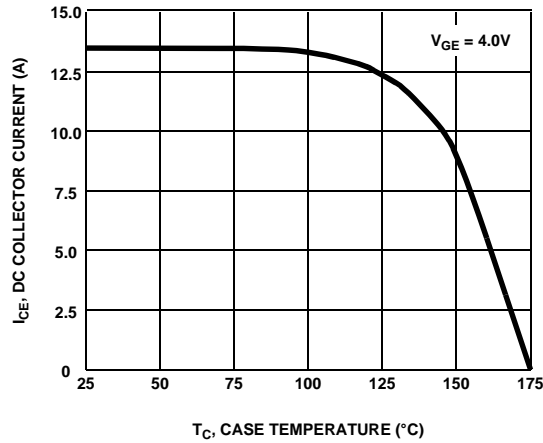


Figure 9. DC Collector Current vs Case Temperature

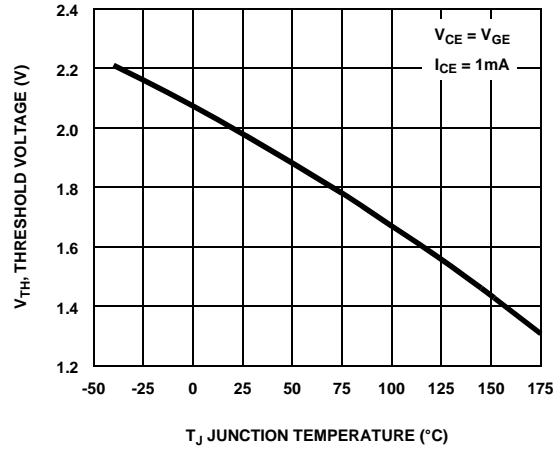


Figure 10. Threshold Voltage vs Junction Temperature

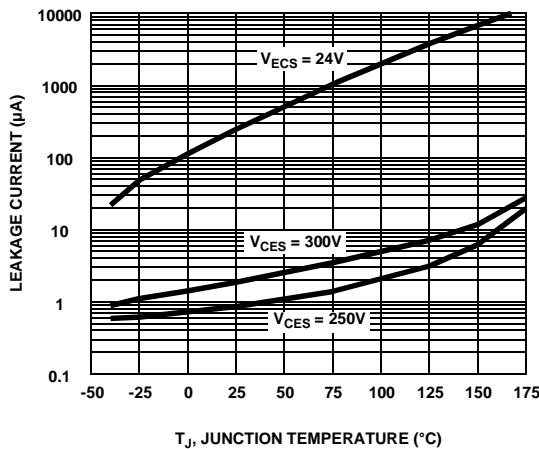


Figure 11. Leakage Current vs Junction Temperature

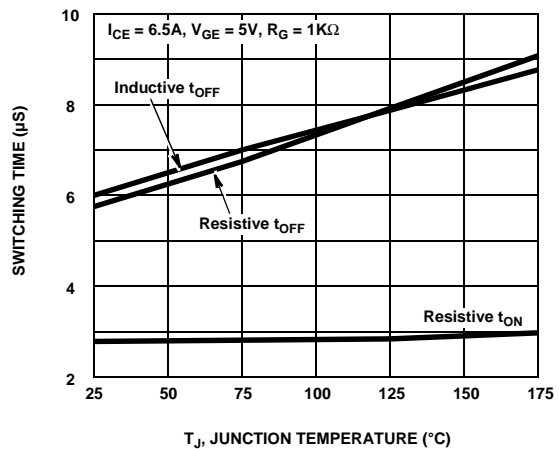


Figure 12. Switching Time vs Junction Temperature

Typical Performance Curves (Continued)

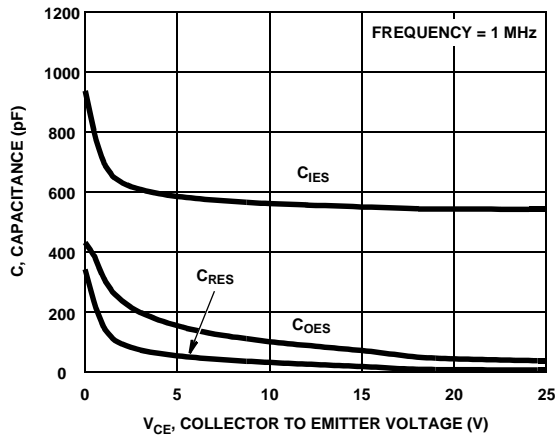


Figure 13. Capacitance vs Collector to Emitter Voltage

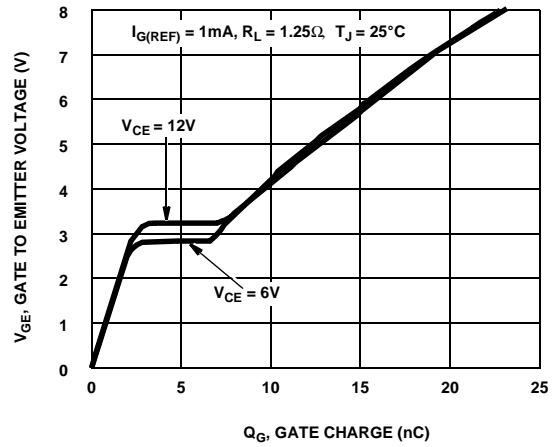


Figure 14. Gate Charge

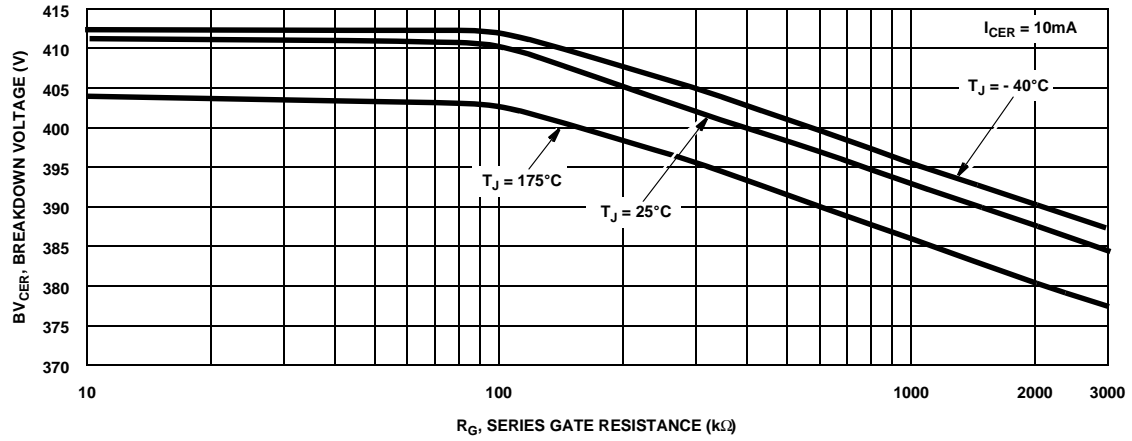


Figure 15. Breakdown Voltage vs Series Gate Resistance

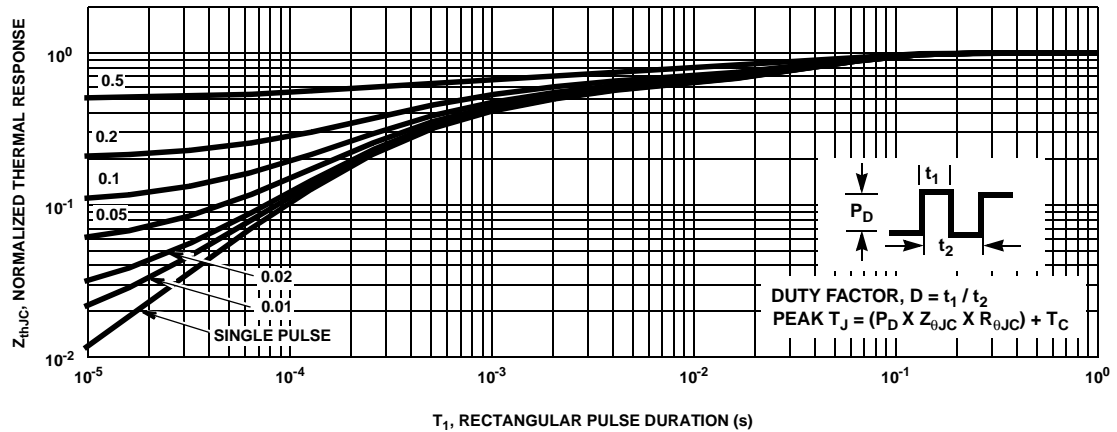


Figure 16. IGBT Normalized Transient Thermal Impedance, Junction to Case

SPICE Thermal Model

REV 25 April 2002

ISL9V2040D3S, ISL9V2040S3S, ISL9V2040P3

CTHERM1 th 6 1.3e -2
 CTHERM2 6 5 8.8e -4
 CTHERM3 5 4 8.8e -3
 CTHERM4 4 3 3.9e -1
 CTHERM5 3 2 3.6e -1
 CTHERM6 2 tl 1.9e -1

RTHERM1 th 6 1.2e -1
 RTHERM2 6 5 3.2e -1
 RTHERM3 5 4 1.7e -1
 RTHERM4 4 3 1.2e -1
 RTHERM5 3 2 1.3e -1
 RTHERM6 2 tl 2.5e -1

SABER Thermal Model

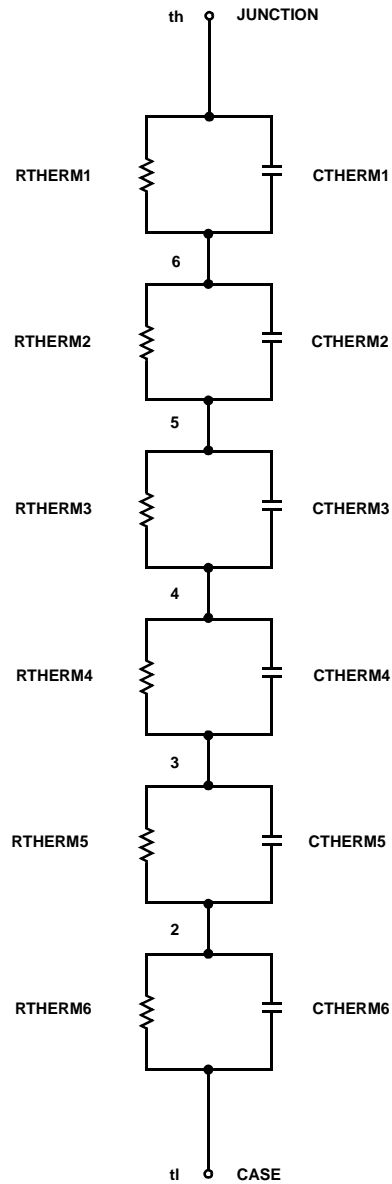
SABER thermal model

ISL9V2040D3S, ISL9V2040S3S, ISL9V2040P3

template thermal_model th tl
 thermal_c th, tl

```
{
  ctherm.ctherm1 th 6 = 1.3e -3
  ctherm.ctherm2 6 5 = 8.8e -4
  ctherm.ctherm3 5 4 = 8.8e -3
  ctherm.ctherm4 4 3 = 3.9e -1
  ctherm.ctherm5 3 2 = 3.6e -1
  ctherm.ctherm6 2 tl = 1.9e -1
```

```
rtherm.rtherm1 th 6 = 1.2e -1
rtherm.rtherm2 6 5 = 3.2e -1
rtherm.rtherm3 5 4 = 1.7e -1
rtherm.rtherm4 4 3 = 1.2e -1
rtherm.rtherm5 3 2 = 1.3e -1
rtherm.rtherm6 2 tl = 2.5e -1
}
```



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DenseTrench TM	GTO TM	POP TM	Stealth TM	
DOME TM	HiSeC TM	Power247 TM	SuperSOT TM -3	
EcoSPARK TM	I ² C TM	PowerTrench [®]	SuperSOT TM -6	
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PRODUCT STATUS DEFINITIONS

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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